MOS FET

FC8V33030L

## **Panasonic**

### FC8V33030L

#### **Dual N-channel MOSFET**

For switching For DC-DC Converter

#### ■ Features

- Low drain-source On-state Resistance : RDS(on) typ = 22 m $\Omega$  (VGS = 4.5 V)
- High-speed switching : Qg = 3.8 nC
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 6A

Established: 2011-04-20

: 2013-07-31

Revised

■ Basic Part Number : Dual Nch MOS 33V (Individual)

#### ■ Packaging

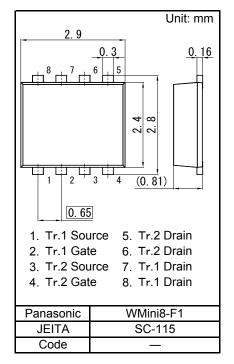
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

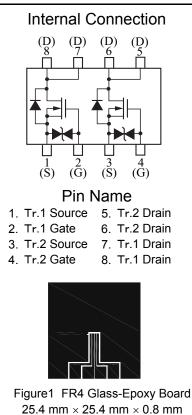
Absolute Maximum Ratings Ta = 25 °C Tr.1, Tr.2

Parameter	Symbol	Rating	Unit			
Drain-source Voltage	VDS	33	V			
Gate-source Voltage	VGS	±20	V			
Drain Current (Steady State) *1	ID	ID 6.5				
Drain Current (t = 10 s) *1	טו	8				
Drain Current (Pulsed) *1,*2	IDp	26	Α			
Source Current (Pulsed)	ISp	6.5				
(Body Diode) *1,*2	(BD)	0.5				
Total Power Dissipation (Steady State) *1	PD	1	W			
Total Power Dissipation (t = 10 s) *1	וו	1.5				
Channel Temperature	Tch	150	°C			
Operating Ambient Temperature	Topr	-40 to + 85	°C			
Storage Temperature Range	Tstg	-55 to +150	°C			

Note) \*1 Device mounted on a glass-epoxy board (See Figure 1)

\*2 Pulse test: Ensure that the channel temperature does not exceed 150°C.





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### ■ Electrical Characteristics Ta = $25^{\circ}$ C $\pm 3^{\circ}$ C Tr.1, Tr.2

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 3.3 A, VGS = 10 V		15	20	mΩ
	RDS(on)2	ID = 3.3 A. VGS = 4.5 V		22	35	

**Dynamic Characteristics** 

Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V	360		
Output Capacitance	Coss	f = 1 MHz	70		pF
Reverse Transfer Capacitance	Crss	1 - 1 1011 12	50		
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V	8		
Rise Time *2	tr	ID = 3.3 A	3		ns
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	24		115
Fall Time *2	tf	ID = 3.3 A	9		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	3.8		
Gate-source Charge	Qgs	ID = 6.5 A	1.4		nC
Gate-drain Charge	Qgd	10 - 0.5 A	1.6	·	

Body	Diode	Characteristic

Diode Forward Voltage *1	VSD	IS = 3.3 A, VGS = 0 V	8.0	1.2	V

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

<sup>2. \*1</sup> Pulse test: Ensure that the channel temperature does not exceed 150°C.

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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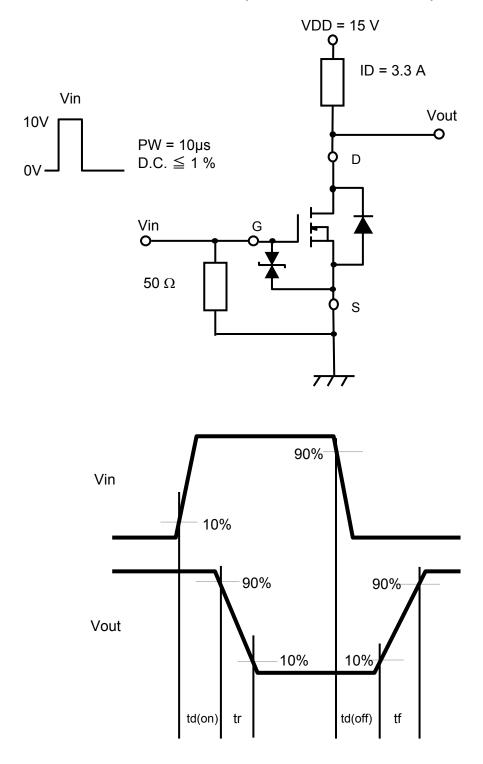
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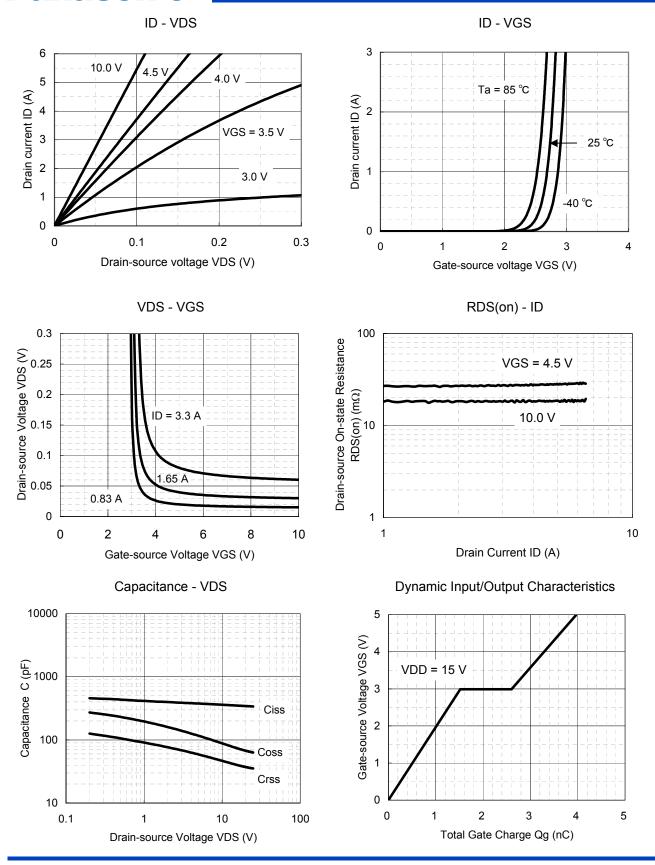
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\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



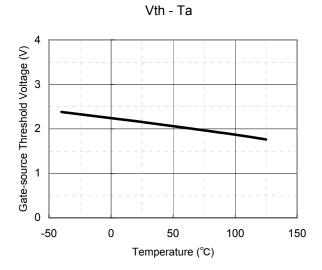
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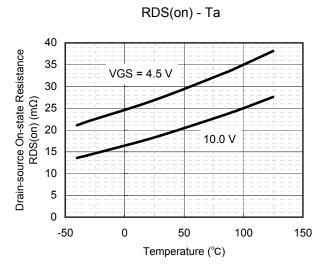


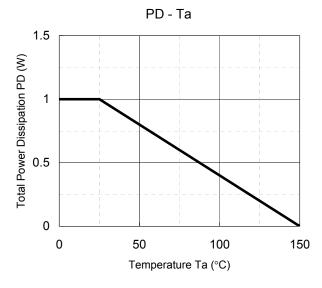
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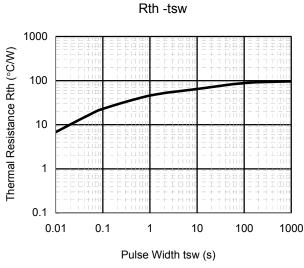
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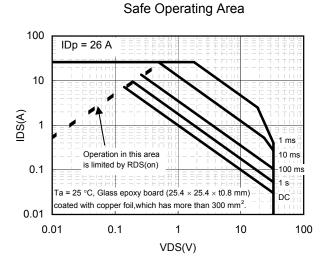
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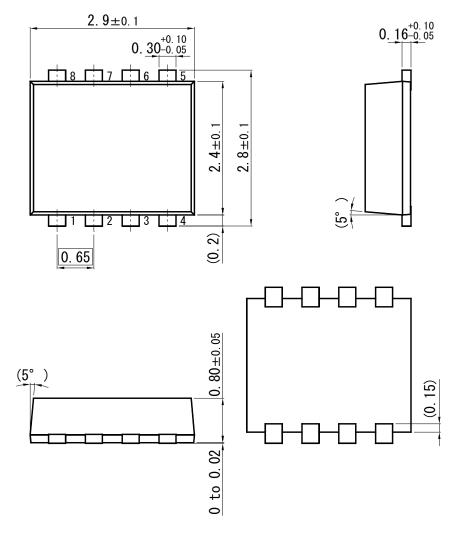


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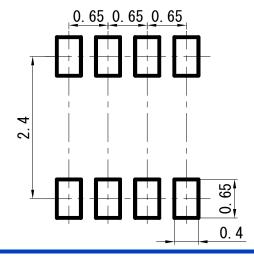
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WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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